

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Tetsuya Taki

**Serial No.:** Not Yet Assigned      **Group Art Unit:** Not Yet Assigned

**Filing Date:** Concurrently Herewith      **Examiner:** Unknown

**For:** METHOD FOR PRODUCING P-TYPE GROUP III NITRIDE COMPOUND SEMICONDUCTOR

Commissioner for Patents  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to Applicants' duty of disclosure under 37 CFR §1.56, Applicant respectfully brings the following documents listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed documents are provided herewith for the convenience of the Examiner. In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3), the relevance of these documents is discussed on pages 2 and 3 of the subject application. Further, English-language Abstracts are attached to some the references.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

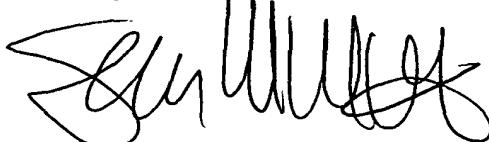
It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Date: 9/22/03

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Respectfully submitted,



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**INFORMATION DISCLOSURE CITATION**  
*(Use several sheets if necessary)*

*(Use several sheets if necessary)*

**Docket Number (Optional)**

T36-160821M/KOH

**Application Number:**

Not Yet Assigned

**Applicant(s)**

Tetsuya Taki

**Filing Date**

#### **Concurrently Herewith**

Group Art Unit

Unknown

## U.S. PATENT DOCUMENTS

## **FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	05-183189	07/23/1993	Japan			AB5	
	05-198841	08/06/1993	Japan			AB5	
	08-097471	04/12/1996	Japan				

**OTHER DOCUMENTS** (*Including Author, Title, Date, Pertinent Pages, Etc.*)

Nakamura, et al., "HOLE COMPENSATION MECHANISM OF P-TYPE GaN FILMS", Jpn. J. App. Phys. Vol. 31 Part 1, No. 5A, May 1992, Pages 1258-1266

Amano, et al., "GaN BLUE AND UV LIGHT EMITTING DIODES WITH A PN JUNCTION", Oyo Buturi, Vol. 60, No. 2, 1991, Pages 163-166

EXAMINER

**DATE CONSIDERED**

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.